a first pad arranged on a wiring level different from said first I/O slot and arranged above the first I/O slot;

a second pad arranged on a wiring level different from said first I/O slot and arranged apart from the peripheral portion of the chip as compared with the first pad;

a first wiring comprising one end positioned in said first pad and comprising the other end positioned in the peripheral portion of the inner region of the chip above the first I/O slot;

a second wiring comprising one end positioned in the second pad and comprising the other end positioned in the peripheral portion of the inner region of the chip above the second I/O slot; and

a third wiring arranged in an outermost peripheral region of the chip and serving to connect the other end of the first wiring to an I/O slot different from the first I/O slot.

10. (Twice Amended) The semiconductor integrated circuit device according to claim 1, further comprising a fourth wiring arranged in an outermost peripheral region of the chip and serving to connect the other end of the second wiring to the first I/O slot, wherein the third wiring is isolated from the second wiring, and the fourth wiring is isolated from the first wiring.

- 15. (New) The semiconductor integrated circuit device according to claim 1, wherein the I/O slot different from the first I/O slot is the second I/O slot.
- 16. (New) The semiconductor integrated circuit device according to claim 1, wherein the first and second pads are arranged on the same wiring level.
- 17. (New) The semiconductor integrated circuit device according to claim 1, wherein the first and second I/O slots are adjacent to each other.

Control

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